

Title (en)  
Organic electronic device, method of producing the same, and method of operating the same

Title (de)  
Organische elektronische Anordnung, Herstellungsmethode und Verwendung

Title (fr)  
Dispositif électronique organique, méthode de sa fabrication et utilisation

Publication  
**EP 1179863 A3 20060118 (EN)**

Application  
**EP 01306846 A 20010810**

Priority  
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Abstract (en)  
[origin: EP1179863A2] An organic electronic device is provided that utilizes a conductive organic thin film having a conductive network in the channel region. The conductive network comprises an organic molecular group made up of organic molecules each having a light-responsive group or a polar group bonded together by conjugated bonds. Thus, high integration and high-speed response is made possible. In addition, a method of producing a functional organic thin film fixed to a specified portion of a substrate surface by covalent bonds is provided. This method comprises preliminarily treating the substrate by performing an active hydrogen exposure treatment on the specified portion (or an active hydrogen removing treatment on the portion other than the specified portion) and reacting the active hydrogens of the specified portion with organic molecules. Thus, a high precision functional organic thin film, even one formed to the micron pattern level, can be provided.

IPC 8 full level  
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